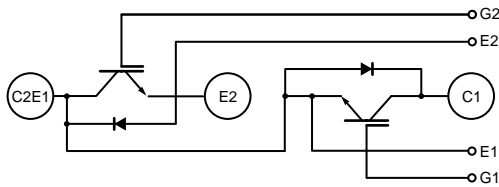
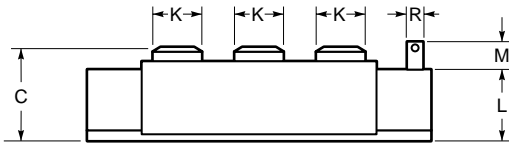
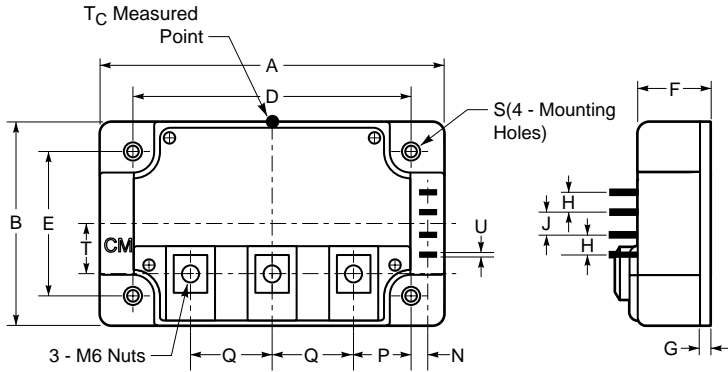


MITSUBISHI IGBT MODULES  
**CM400DU-12H**  
 HIGH POWER SWITCHING USE  
 INSULATED TYPE



Outline Drawing and Circuit Diagram

Dimensions	Inches	Millimeters
A	4.25	108.0
B	2.44	62.0
C	1.14 +0.04/-0.02	29 +1.0/-0.5
D	3.66±0.01	93.0±0.25
E	1.88±0.01	48.0±0.25
F	0.87	22.0
G	0.16	4.0
H	0.24	6.0
J	0.59	15.0

Dimensions	Inches	Millimeters
K	0.71	18.0
L	0.87	22.0
M	0.33	8.5
N	0.10	2.5
P	0.85	21.5
Q	0.98	25.0
R	0.11	2.8
S	0.25 Dia.	6.5 Dia.
T	0.6	15.15



**Description:**

Mitsubishi IGBT Modules are designed for use in switching applications. Each module consists of two IGBTs in a half-bridge configuration with each transistor having a reverse-connected super-fast recovery free-wheel diode. All components and interconnects are isolated from the heat sinking baseplate, offering simplified system assembly and thermal management.

**Features:**

- Low Drive Power
- Low  $V_{CE(sat)}$
- Discrete Super-Fast Recovery Free-Wheel Diode
- High Frequency Operation
- Isolated Baseplate for Easy Heat Sinking

**Applications:**

- AC Motor Control
- Motion/Servo Control
- UPS
- Welding Power Supplies

**Ordering Information:**

Example: Select the complete module number you desire from the table - i.e. CM400DU-12H is a 600V ( $V_{CES}$ ), 400 Ampere Dual IGBT Module.

Type	Current Rating Amperes	$V_{CES}$ Volts (x 50)
CM	400	12

## CM400DU-12H

HIGH POWER SWITCHING USE  
INSULATED TYPEAbsolute Maximum Ratings,  $T_j = 25\text{ }^\circ\text{C}$  unless otherwise specified

Ratings	Symbol	CM400DU-12H	Units
Junction Temperature	$T_j$	-40 to 150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-40 to 125	$^\circ\text{C}$
Collector-Emitter Voltage (G-E SHORT)	$V_{CES}$	600	Volts
Gate-Emitter Voltage (C-E SHORT)	$V_{GES}$	$\pm 20$	Volts
Collector Current ( $T_c = 25^\circ\text{C}$ )	$I_C$	400	Amperes
Peak Collector Current ( $T_j \leq 150^\circ\text{C}$ )	$I_{CM}$	800*	Amperes
Emitter Current** ( $T_c = 25^\circ\text{C}$ )	$I_E$	400	Amperes
Peak Emitter Current**	$I_{EM}$	800*	Amperes
Maximum Collector Dissipation ( $T_c = 25^\circ\text{C}$ )	$P_C$	1130	Watts
Mounting Torque, M6 Main Terminal	–	3.5–4.5	N · m
Mounting Torque, M6 Mounting	–	3.5–4.5	N · m
Weight	–	400	Grams
Isolation Voltage (Main Terminal to Baseplate, AC 1 min.)	$V_{iso}$	2500	Vrms

\* Pulse width and repetition rate should be such that the device junction temperature ( $T_j$ ) does not exceed  $T_{j(max)}$  rating.

\*\*Represents characteristics of the anti-parallel, emitter-to-collector free-wheel diode (FWDi).

Static Electrical Characteristics,  $T_j = 25\text{ }^\circ\text{C}$  unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Collector-Cutoff Current	$I_{CES}$	$V_{CE} = V_{CES}, V_{GE} = 0V$	–	–	1	mA
Gate Leakage Voltage	$I_{GES}$	$V_{GE} = V_{GES}, V_{CE} = 0V$	–	–	0.5	$\mu\text{A}$
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	$I_C = 40\text{mA}, V_{CE} = 10V$	4.5	6	7.5	Volts
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 400\text{A}, V_{GE} = 15V, T_j = 25^\circ\text{C}$	–	2.4	3.0	Volts
		$I_C = 400\text{A}, V_{GE} = 15V, T_j = 125^\circ\text{C}$	–	2.6	–	Volts
Total Gate Charge	$Q_G$	$V_{CC} = 300V, I_C = 400\text{A}, V_{GE} = 15V$	–	800	–	nC
Emitter-Collector Voltage*	$V_{EC}$	$I_E = 400\text{A}, V_{GE} = 0V$	–	–	2.6	Volts

\* Pulse width and repetition rate should be such that the device junction temperature ( $T_j$ ) does not exceed  $T_{j(max)}$  rating.Dynamic Electrical Characteristics,  $T_j = 25\text{ }^\circ\text{C}$  unless otherwise specified

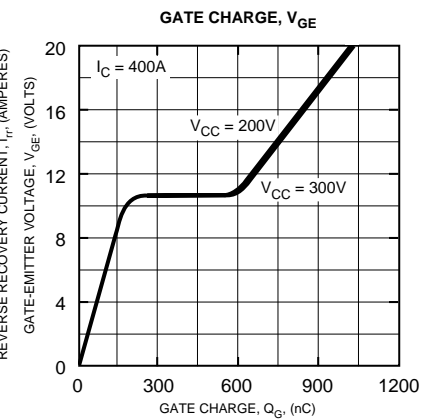
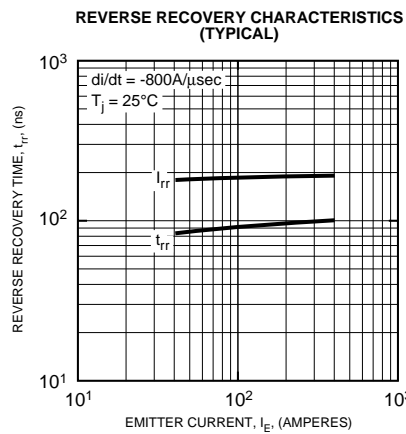
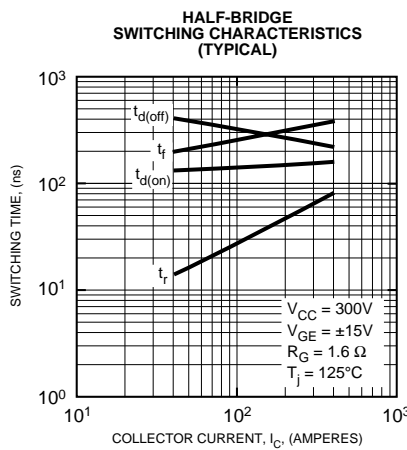
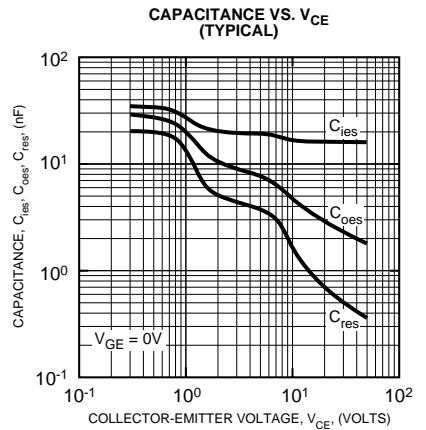
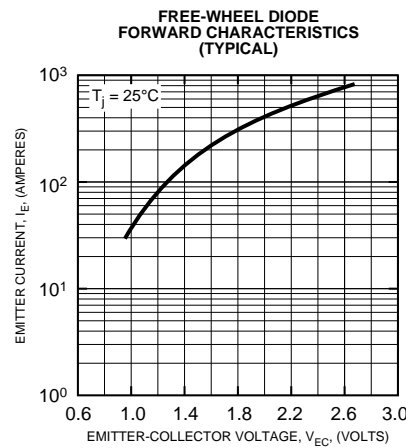
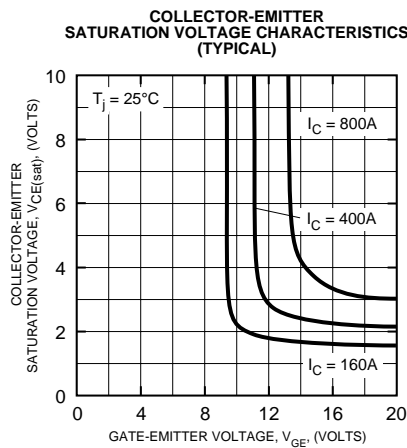
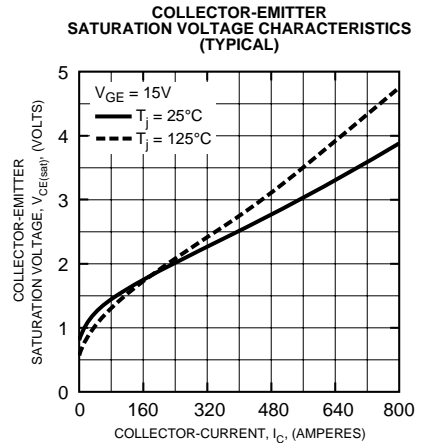
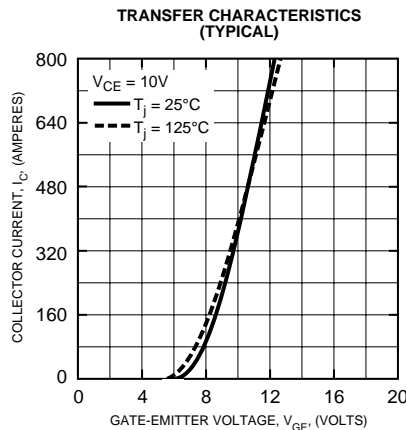
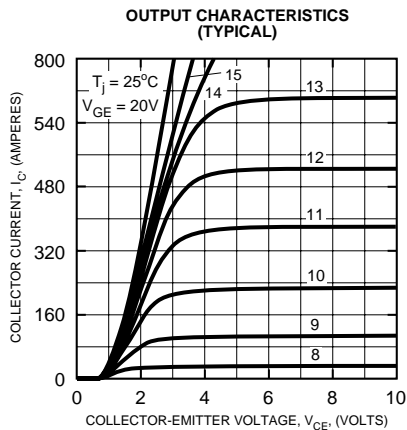
Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Input Capacitance	$C_{ies}$		–	–	35.2	nF
Output Capacitance	$C_{oes}$	$V_{CE} = 10V, V_{GE} = 0V$	–	–	19.2	nF
Reverse Transfer Capacitance	$C_{res}$		–	–	5.2	nF
Resistive	Turn-on Delay Time	$V_{CC} = 300V, I_C = 400\text{A},$ $V_{GE1} = V_{GE2} = 15V,$ $R_G = 1.6\Omega, \text{Resistive}$	–	–	250	ns
	Rise Time					
Load	Turn-off Delay Time	Load Switching Operation	–	–	350	ns
	Fall Time					
Diode Reverse Recovery Time	$t_{rr}$	$I_E = 400\text{A}, di_E/dt = -800\text{A}/\mu\text{s}$	–	–	160	ns
Diode Reverse Recovery Charge	$Q_{rr}$	$I_E = 400\text{A}, di_E/dt = -800\text{A}/\mu\text{s}$	–	0.96	–	$\mu\text{C}$

Thermal and Mechanical Characteristics,  $T_j = 25\text{ }^\circ\text{C}$  unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance, Junction to Case	$R_{th(j-c)Q}$	Per IGBT 1/2 Module	–	–	0.11	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Case	$R_{th(j-c)D}$	Per FWDi 1/2 Module	–	–	0.18	$^\circ\text{C}/\text{W}$
Contact Thermal Resistance	$R_{th(c-f)}$	Per Module, Thermal Grease Applied	–	0.020	–	$^\circ\text{C}/\text{W}$

# CM400DU-12H

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